## 固物 2018 期末答案

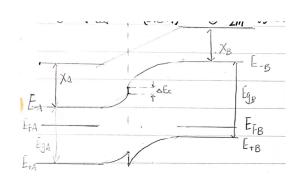
## Deschain

## 2022年6月17日

1.

- (1) ①X 射线衍射/中子衍射/电子衍射②中子非弹性散射/拉曼散射/布里渊散射/光子非弹性散射/X 射线 散射/X 射线衍射(写出一种即可)
- (2) ①电子的自旋磁矩②电子的轨道磁矩③电子的感生磁矩④铁磁性⑤亚铁磁性⑥反铁磁性⑦正⑧负
- (3) ①定向②晶格
- (4) ①迁移率②载流子浓度③总掺杂
- (5)  $\mathfrak{D}[-\frac{\pi}{2a}, \frac{\pi}{2a}] \mathfrak{D}\sqrt{15} : 1$
- (6)  $@24N_A @21N_A @3N_A @\frac{4\pi}{G}$
- (7)  $\textcircled{1} \frac{A}{r^6} \textcircled{2} \frac{B}{r^{12}} \textcircled{3} \sqrt[6]{\frac{2B}{A}} \textcircled{4} \frac{NA^2}{8B}$ (8)  $\textcircled{1}4.14 \times 10^{-15} J \textcircled{2}8.48^{\circ}$
- (9)  $@38.4cm/\Omega(\mu_n = 300, \mu_p = 150)$
- (10)  $@-1.28 \times 10^{-5} m^3 / C @4.88 \times 10^{23} m^{-3}$
- (11)  $@1.57 \times 10^6 m/s @6.3 \times 10^{-30} @9.9 \times 10^{-24}$
- (12) ①独立②统一
- (13) ①球面② $(3\pi^2n)^{\frac{1}{3}}$ ③ $\frac{\hbar^2}{2m}(3\pi^2n)^{\frac{2}{3}}$ ④略低

2.)



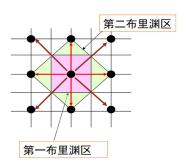
$$\Delta E_C = \chi_A - \chi_B = 0.17eV$$

$$\Delta E_V = |\chi_A + E_{g_A} - (\chi_B + E_{g_B})| = 0.3eV$$

$$V_D = |\frac{1}{e}(E_{F_A} - E_{F_B})| = 0.3V$$

3.

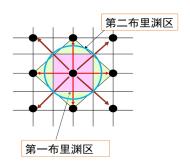
(1)



(2)

$$k_F = \sqrt{2\pi n} = \sqrt{\frac{\pi}{2A^2}}$$

(3)



4.

$$(1) \\ n_{iSi} = (N_- N_+)^{\frac{1}{2}} e^{-\frac{Eg_{Si}}{2k_BT}} = \frac{2}{h^3} (2\pi k_B T)^{\frac{3}{2}} (m_n^* m_p^*)^{\frac{3}{4}} e^{-\frac{Eg_{Si}}{2k_BT}} = 9.40 \times 10^{11} cm^{-3} < N_D \\ n_{iGe} = (N_- N_+)^{\frac{1}{2}} e^{-\frac{Eg_{Ge}}{2k_BT}} = \frac{2}{h^3} (2\pi k_B T)^{\frac{3}{2}} (m_n^* m_p^*)^{\frac{3}{4}} e^{-\frac{Eg_{Ge}}{2k_BT}} = 2.15 \times 10^{14} cm^{-3} > N_D$$

(2) Si 可以形成 N 结

(3)

$$V_D = \frac{1}{e}(E_{Fn} - E_{Fp}) = \frac{k_B T}{e} ln(\frac{N_D N_A}{n_{iSi}^2}) = 0.3745V$$

5.

$$\begin{split} W(x) &= \sum V_n e^{j\frac{2\pi n}{a}x}, V_n = \frac{1}{a} \int_{-\frac{a}{2}}^{\frac{a}{2}} W(x) e^{-j\frac{2\pi n}{a}x} dx = \frac{2V_0}{a} cos(\frac{2\pi nb}{a}) \\ V_{g_1} &= |2V_1| = \frac{4V_0}{a} cos(\frac{2b}{a}\pi), V_{g_2} = |2V_2| = \frac{4V_0}{a} cos(\frac{4b}{a}\pi) \end{split}$$

- (2) a > 4b 不是导体, a = 4b 是导体。
- (3) a = 8b